

	<b>Hit s</b>	<b>Search Text</b>	<b>DBs</b>
24	3	((resist or photoresist) same pattern) and ((pattern or hole or via or (line near6 space)) same (aspect near5 ratio) same LSI) and ((aspect near7 ratio) near20 (VLSI or LSI)) and ((reduct\$4 or increas\$4 or percentage or deviation or uniform\$5 or variation or vary\$4 or difference) same (LSI or pattern or opening or via or hole or trench) same (resist or photoresist) same (heat\$4 or bak\$4 or anneal\$4 or (surface near9 roughness)))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
25	23	((resist or photoresist) same pattern) and ((pattern or hole or via or (line near6 space)) same (aspect near5 ratio) same LSI) and ((aspect near7 ratio) near20 (VLSI or LSI)) and ((reduct\$4 or increas\$4 or percentage or deviation or uniform\$5) same ( LSI or pattern or opening or via or hole or trench) same (resist or photoresist))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB